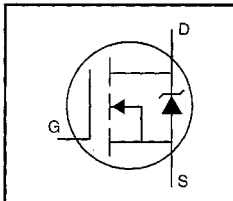


### HEXFET® Power MOSFET

- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements



$$V_{DSS} = 200V$$

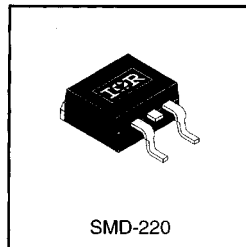
$$R_{DS(on)} = 0.40\Omega$$

$$I_D = 9.0A$$

### Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SMD-220 is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The SMD-220 is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



SMD-220

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### Absolute Maximum Ratings

|                           | Parameter                                 | Max.                  | Units |
|---------------------------|---|-----------------------|-------|
| $I_D @ T_C = 25^\circ C$  | Continuous Drain Current, $V_{GS} @ 10 V$ | 9.0                   | A     |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10 V$ | 5.7                   |       |
| $I_{DM}$                  | Pulsed Drain Current ①                    | 36                    |       |
| $P_D @ T_C = 25^\circ C$  | Power Dissipation                         | 74                    | W     |
| $P_D @ T_A = 25^\circ C$  | Power Dissipation (PCB Mount)**           | 3.0                   |       |
|                           | Linear Derating Factor                    | 0.59                  | W/°C  |
|                           | Linear Derating Factor (PCB Mount)**      | 0.025                 |       |
| $V_{GS}$                  | Gate-to-Source Voltage                    | $\pm 20$              | V     |
| $E_{AS}$                  | Single Pulse Avalanche Energy ②           | 250                   | mJ    |
| $I_{AR}$                  | Avalanche Current ①                       | 9.0                   | A     |
| $E_{AR}$                  | Repetitive Avalanche Energy ①             | 7.4                   | mJ    |
| dv/dt                     | Peak Diode Recovery dv/dt ③               | 5.0                   | V/ns  |
| $T_J, T_{STG}$            | Junction and Storage Temperature Range    | -55 to +150           | °C    |
|                           | Soldering Temperature, for 10 seconds     | 300 (1.6mm from case) |       |


### Thermal Resistance

|                 | Parameter                         | Min. | Typ. | Max. | Units |
|-----------------|-----------------------------------|------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case                  | —    | —    | 1.7  | °C/W  |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB mount)** | —    | —    | 40   |       |
| $R_{\theta JA}$ | Junction-to-Ambient               | —    | —    | 62   |       |


\*\* When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

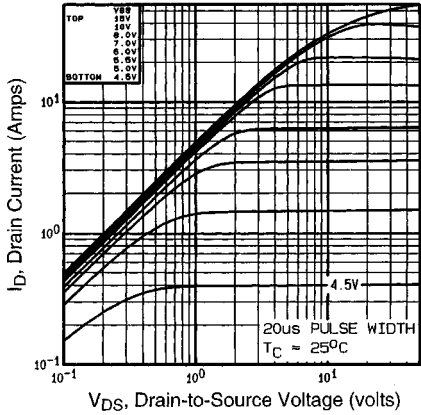
|                                 | Parameter                            | Min. | Typ. | Max. | Units              | Test Conditions  |
|---------------------------------|--------------------------------------|------|------|------|--------------------|--|
| $V_{(BR)DSS}$                   | Drain-to-Source Breakdown Voltage    | 200  | —    | —    | V                  | $V_{GS}=0V, I_D=250\mu A$  |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient  | —    | 0.24 | —    | $V/^\circ\text{C}$ | Reference to $25^\circ\text{C}, I_D=1\text{mA}$                                    |
| $R_{DS(on)}$                    | Static Drain-to-Source On-Resistance | —    | —    | 0.40 | $\Omega$           | $V_{GS}=10V, I_D=5.4A$ ④   |
| $V_{GS(th)}$                    | Gate Threshold Voltage               | 2.0  | —    | 4.0  | V                  | $V_{DS}=V_{GS}, I_D=250\mu A$  |
| $g_{fs}$                        | Forward Transconductance             | 3.8  | —    | —    | S                  | $V_{DS}=50V, I_D=5.4A$ ④   |
| $I_{DSS}$                       | Drain-to-Source Leakage Current      | —    | —    | 25   | $\mu A$            | $V_{DS}=200V, V_{GS}=0V$   |
|                                 |                                      | —    | —    | 250  |                    | $V_{DS}=160V, V_{GS}=0V, T_J=125^\circ\text{C}$                                    |
| $I_{GSS}$                       | Gate-to-Source Forward Leakage       | —    | —    | 100  | nA                 | $V_{GS}=20V$   |
|                                 | Gate-to-Source Reverse Leakage       | —    | —    | -100 |                    | $V_{GS}=-20V$  |
| $Q_g$                           | Total Gate Charge                    | —    | —    | 43   | nC                 | $I_D=5.9A$   |
| $Q_{gs}$                        | Gate-to-Source Charge                | —    | —    | 7.0  |                    | $V_{DS}=160V$  |
| $Q_{gd}$                        | Gate-to-Drain ("Miller") Charge      | —    | —    | 23   |                    | $V_{GS}=10V$ See Fig. 6 and 13 ④   |
| $t_{d(on)}$                     | Turn-On Delay Time                   | —    | 9.4  | —    | ns                 | $V_{DD}=100V$  |
| $t_r$                           | Rise Time                            | —    | 28   | —    |                    | $I_D=5.9A$   |
| $t_{d(off)}$                    | Turn-Off Delay Time                  | —    | 39   | —    |                    | $R_G=12\Omega$   |
| $t_f$                           | Fall Time                            | —    | 20   | —    |                    | $R_D=16\Omega$ See Figure 10 ④   |
| $L_D$                           | Internal Drain Inductance            | —    | 4.5  | —    | nH                 | Between lead, 6 mm (0.25in.) from package and center of die contact                |
| $L_S$                           | Internal Source Inductance           | —    | 7.5  | —    |                    |  |
| $C_{iss}$                       | Input Capacitance                    | —    | 800  | —    | pF                 | $V_{GS}=0V$  |
| $C_{oss}$                       | Output Capacitance                   | —    | 240  | —    |                    | $V_{DS}=25V$   |
| $C_{rss}$                       | Reverse Transfer Capacitance         | —    | 76   | —    |                    | $f=1.0\text{MHz}$ See Figure 5   |

## Source-Drain Ratings and Characteristics

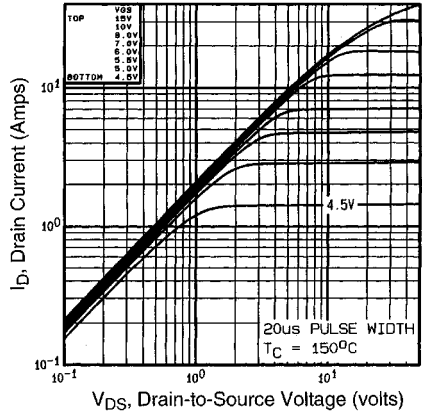
|          | Parameter                              | Min.  | Typ. | Max. | Units         | Test Conditions   |
|----------|--|---|------|------|---------------|---|
| $I_S$    | Continuous Source Current (Body Diode) | —   | —    | 9.0  | A             | MOSFET symbol showing the integral reverse p-n junction diode.  |
| $I_{SM}$ | Pulsed Source Current (Body Diode) ①   | —   | —    | 36   |               |   |
| $V_{SD}$ | Diode Forward Voltage                  | —   | —    | 2.0  | V             | $T_J=25^\circ\text{C}, I_S=9.0A, V_{GS}=0V$ ④   |
| $t_{rr}$ | Reverse Recovery Time                  | —   | 170  | 340  | ns            | $T_J=25^\circ\text{C}, I_F=5.9A$  |
| $Q_{rr}$ | Reverse Recovery Charge                | —   | 1.1  | 2.2  | $\mu\text{C}$ | $di/dt=100A/\mu\text{s}$ ④  |
| $t_{on}$ | Forward Turn-On Time                   | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ ) |      |      |               |   |

### Notes:

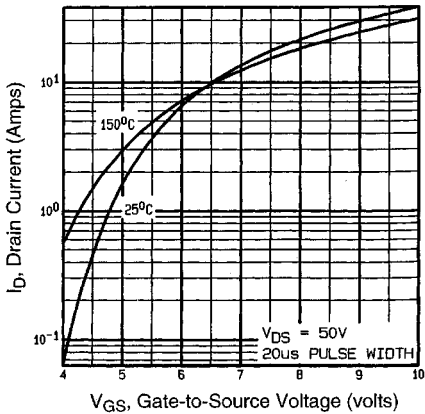
- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ②  $V_{DD}=50V$ , starting  $T_J=25^\circ\text{C}$ ,  $L=4.6\text{mH}$ ,  $R_G=25\Omega$ ,  $I_{AS}=9.0A$  (See Figure 12)
- ③  $I_{SD}\leq 9.0A$ ,  $di/dt\leq 120A/\mu\text{s}$ ,  $V_{DD}\leq V_{(BR)DSS}$ ,  $T_J\leq 150^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .



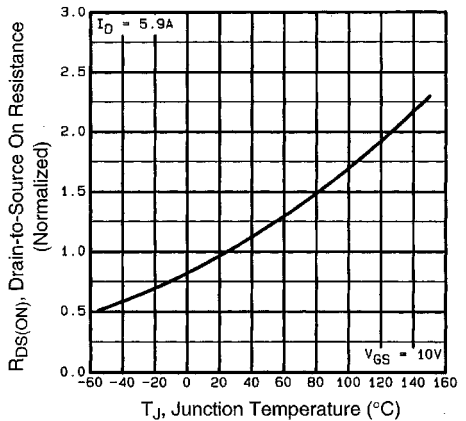
**Fig 1.** Typical Output Characteristics,  $T_C=25^\circ\text{C}$



**Fig 2.** Typical Output Characteristics,  $T_C=150^\circ\text{C}$

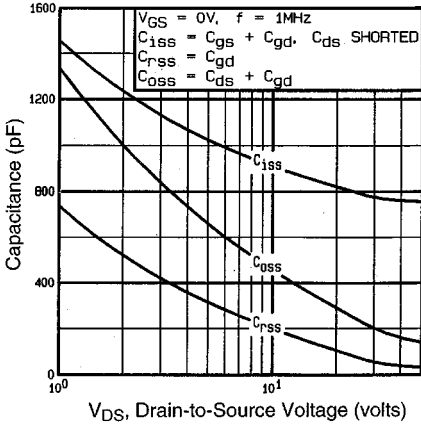


**Fig 3.** Typical Transfer Characteristics

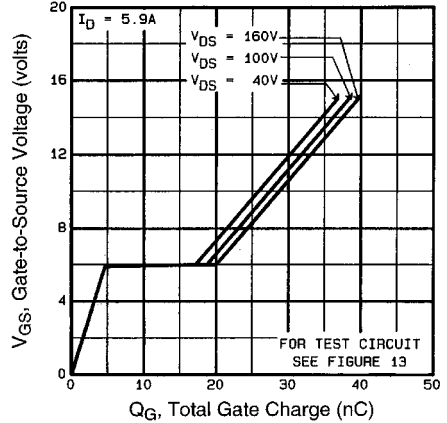


**Fig 4.** Normalized On-Resistance Vs. Temperature

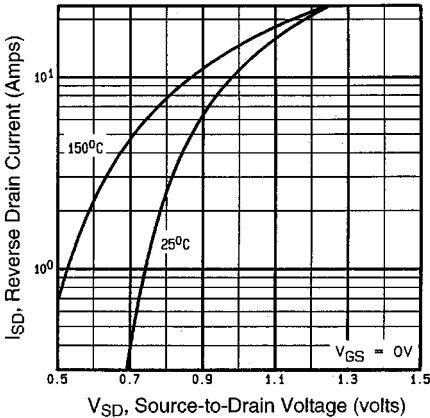
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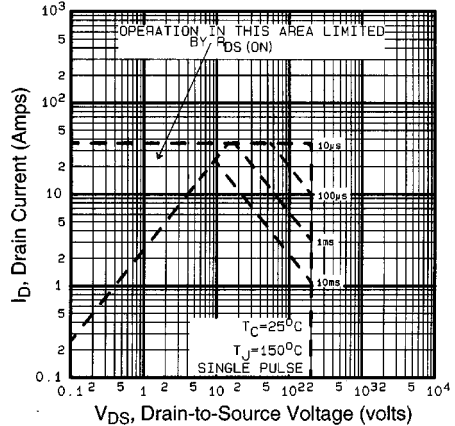
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



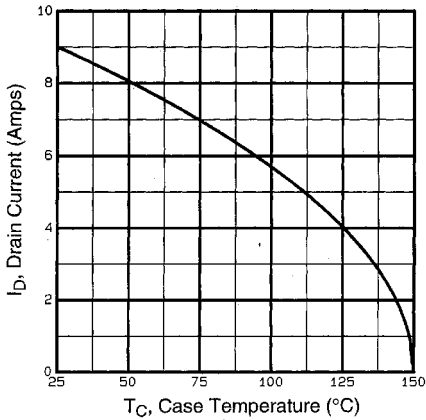
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



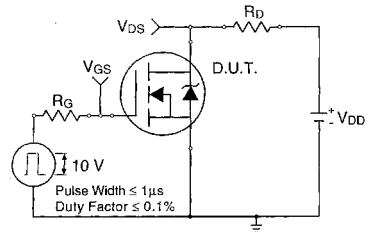
**Fig 7.** Typical Source-Drain Diode Forward Voltage



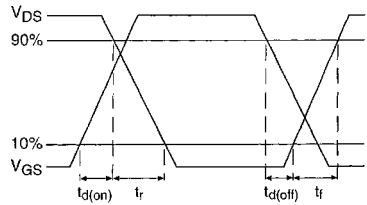
**Fig 8.** Maximum Safe Operating Area



**Fig 9.** Maximum Drain Current Vs. Case Temperature

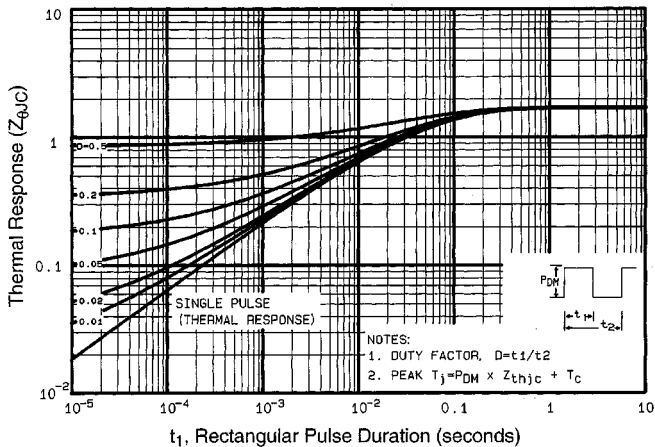


**Fig 10a.** Switching Time Test Circuit

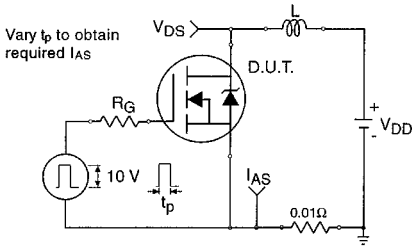


**Fig 10b.** Switching Time Waveforms

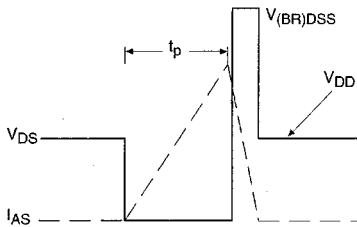
DATA SHEETS



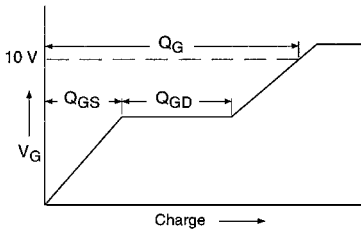
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



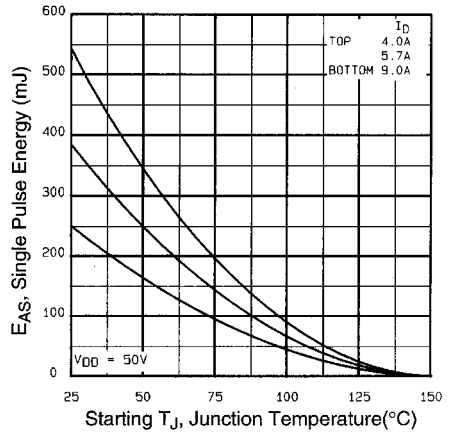
**Fig 12a.** Unclamped Inductive Test Circuit



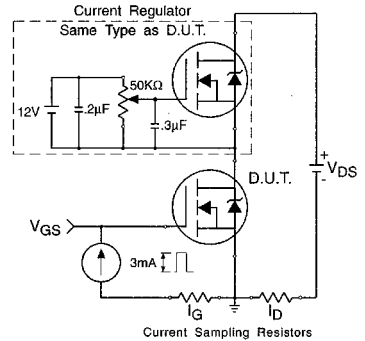
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit

**Appendix A:** Figure 14, Peak Diode Recovery  $dv/dt$  Test Circuit – See page 1505

**Appendix B:** Package Outline Mechanical Drawing – See page 1507

**Appendix C:** Part Marking Information – See page 1515

**Appendix D:** Tape & Reel Information – See page 1519